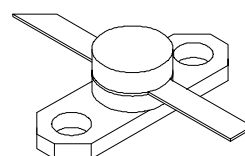


## RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

- REFRACTORY/GOLD METALLIZATION
- EMITTER SITE BALLASTED
- $\infty:1$  VSWR CAPABILITY
- LOW THERMAL RESISTANCE
- INPUT MATCHING
- OVERLAY GEOMETRY
- METAL/CERAMIC HERMETIC PACKAGE
- $P_{OUT} = 35$  W MIN. WITH 10.7 dB GAIN



**.280 2LFL (S068)**

epoxy sealed

**ORDER CODE**

MSC81035M

**BRANDING**

81035M

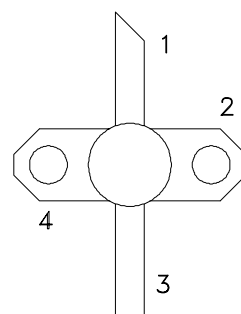
### DESCRIPTION

The MSC81035M is a medium power Class C transistor designed specifically for pulsed L-Band avionics applications. This device is a direct replacement for the MSC1035M. MSC81035M offers improved saturated output power and collector efficiency based on the test circuit described herein.

Low RF thermal resistance and computerized automatic wire bonding techniques ensure high reliability and product consistency.

The MSC81035M is housed in the IMPAC™ package with internal input matching.

### PIN CONNECTION



1. Collector

2. Base

3. Emitter

4. Base

### ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}\text{C}$ )

Symbol	Parameter	Value	Unit
$P_{DISS}$	Power Dissipation* ( $T_C \leq 100^{\circ}\text{C}$ )	150	W
$I_C$	Device Current*	3.0	A
$V_{CC}$	Collector-Supply Voltage*	55	V
$T_J$	Junction Temperature (Pulsed RF Operation)	250	$^{\circ}\text{C}$
$T_{STG}$	Storage Temperature	- 65 to +200	$^{\circ}\text{C}$

### THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance*	1.0	$^{\circ}\text{C/W}$
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\*Applies only to rated RF amplifier operation

Note: Thermal Resistance determined by Infra-Red Scanning of Hot-Spot Junction Temperature at rated RF operating conditions.

## MSC81035M

### ELECTRICAL SPECIFICATIONS ( $T_{\text{case}} = 25^{\circ}\text{C}$ )

#### STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
$BV_{\text{CBO}}$	$I_{\text{C}} = 10 \text{ mA}$	$I_{\text{E}} = 0 \text{ mA}$	65	—	—	V
$BV_{\text{EBO}}$	$I_{\text{E}} = 1 \text{ mA}$	$I_{\text{C}} = 0 \text{ mA}$	3.5	—	—	V
$BV_{\text{CER}}$	$I_{\text{C}} = 10 \text{ mA}$	$R_{\text{BE}} = 10 \Omega$	65	—	—	V
$I_{\text{CES}}$	$V_{\text{BE}} = 0 \text{ V}$	$V_{\text{CE}} = 50 \text{ V}$	—	—	5	mA
$h_{\text{FE}}$	$V_{\text{CE}} = 5 \text{ V}$	$I_{\text{C}} = 500 \text{ mA}$	15	—	120	—

#### DYNAMIC

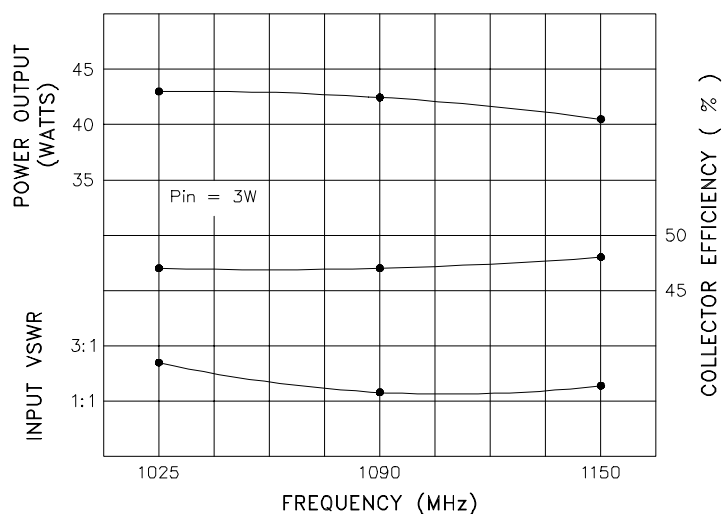
Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
$P_{\text{OUT}}$	$f = 1025 - 1150 \text{ MHz}$	$P_{\text{IN}} = 3.0 \text{ W}$	$V_{\text{CC}} = 50 \text{ V}$	35	40	—	W
$\eta_{\text{C}}$	$f = 1025 - 1150 \text{ MHz}$	$P_{\text{IN}} = 3.0 \text{ W}$	$V_{\text{CC}} = 50 \text{ V}$	40	—	—	%
$P_{\text{G}}$	$f = 1025 - 1150 \text{ MHz}$	$P_{\text{IN}} = 3.0 \text{ W}$	$V_{\text{CC}} = 50 \text{ V}$	10.7	11.2	—	dB

Note: Pulse Width =  $10\mu\text{Sec}$

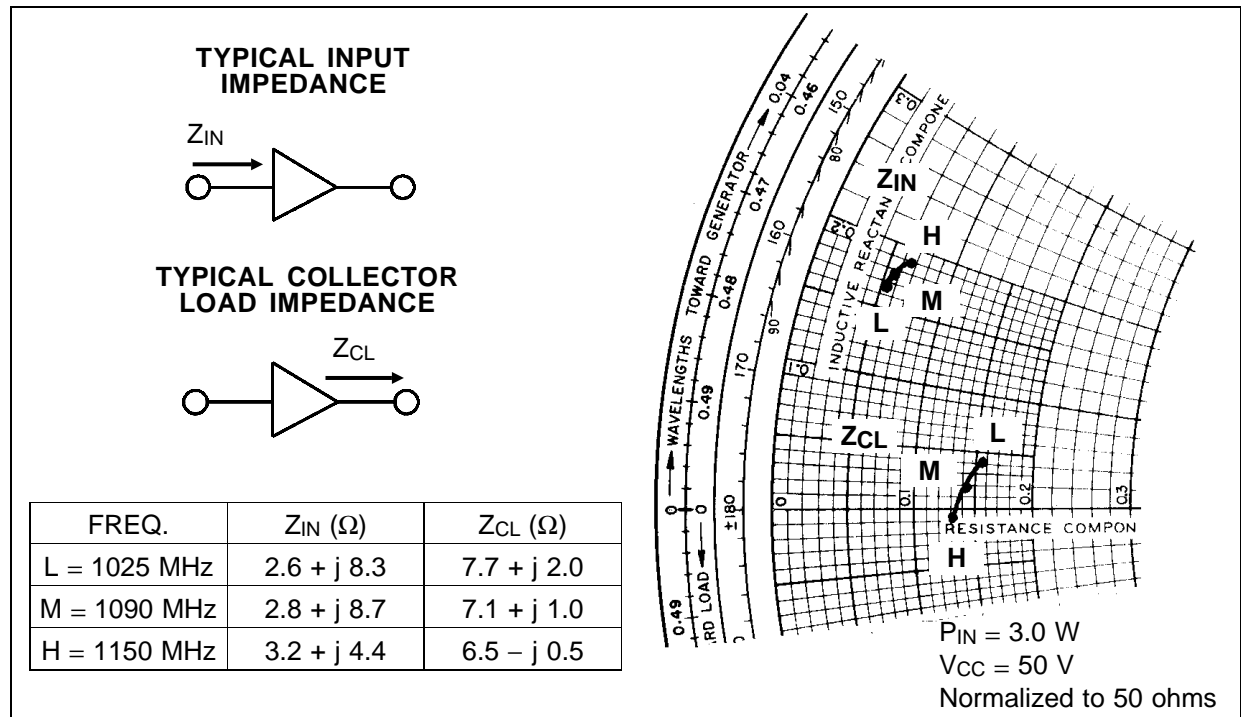
Duty Cycle = 1%

#### TYPICAL PERFORMANCE

##### TYPICAL BROADBAND POWER AMPLIFIER

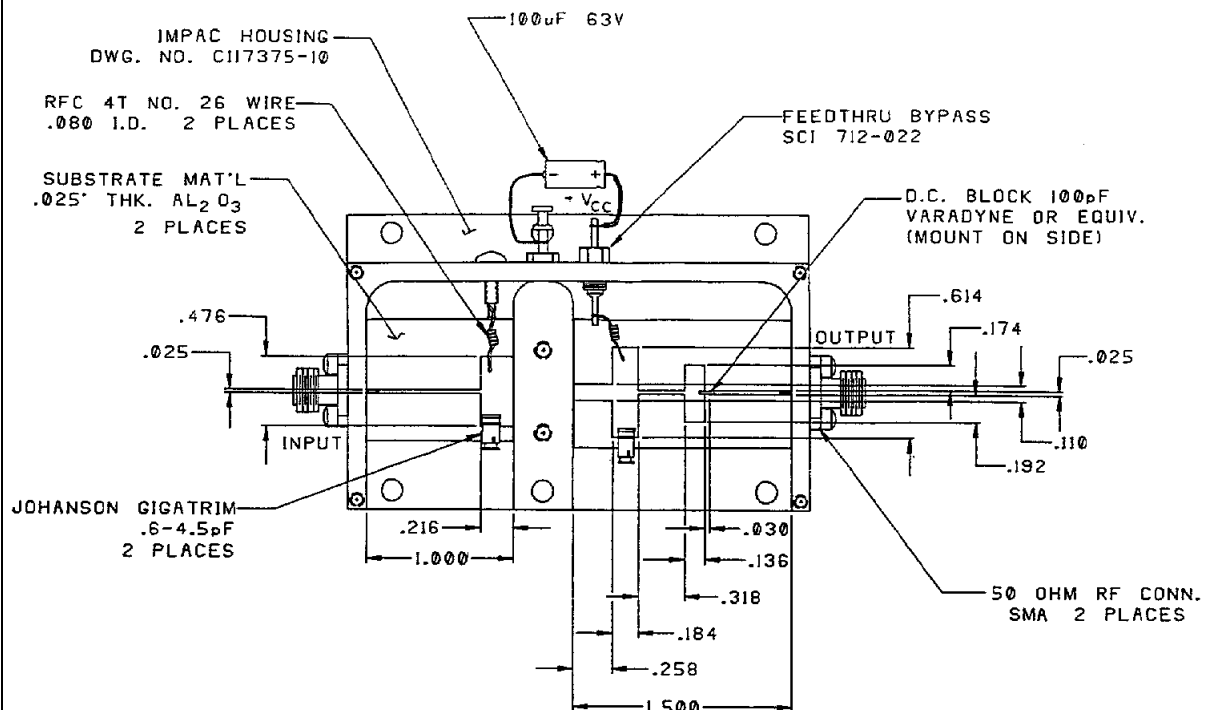


## IMPEDANCE DATA



## TEST CIRCUIT

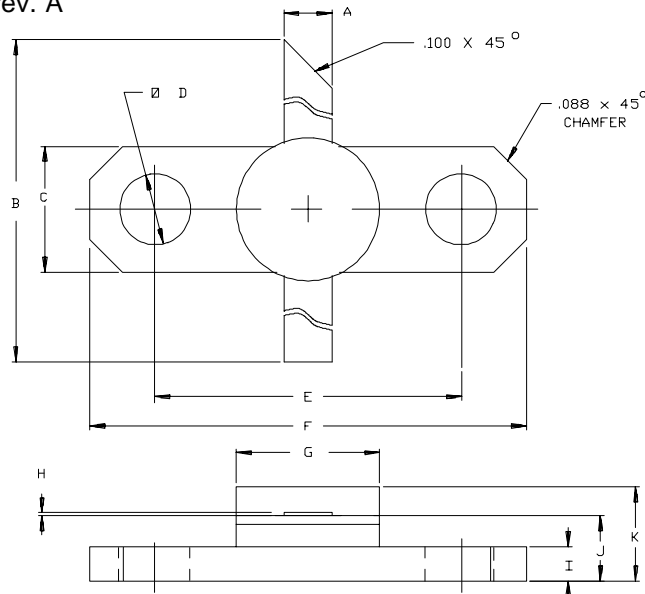
Ref.: Dwg. No. 101 002888



All dimensions are in inches.

PACKAGE MECHANICAL DATA

Ref.: Dwg. No. 12-0218 rev. A



SGS-THOMSON MICROELECTRONICS			CONT'D		
	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.095/2,41	.105/2,67	I	.052/1,32	.072/1,83
B	1.050/26,67		J	.120/3,05	.130/3,30
C	.245/6,22	.255/6,48	K		.210/5,33
D	.120/3,05	.140/3,56			
E	.552/14,02	.572/14,53			
F	.790/20,07	.810/20,57			
G		.285/7,24			
H	.003/0,08	.007/0,18			

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